

# NTHD5903T1

## Power MOSFET Dual P-Channel ChipFET™

### 2.1 Amps, 20 Volts

#### Features

- Low  $R_{DS(on)}$  for Higher Efficiency
- Logic Level Gate Drive
- Miniature ChipFET Surface Mount Package Saves Board Space

#### Applications

- Power Management in Portable and Battery-Powered Products; i.e., Cellular and Cordless Telephones and PCMCIA Cards

#### MAXIMUM RATINGS ( $T_A = 25^\circ\text{C}$ unless otherwise noted)

Rating	Symbol	5 secs	Steady State	Unit
Drain-Source Voltage	$V_{DS}$	-20		V
Gate-Source Voltage	$V_{GS}$	$\pm 12$		V
Continuous Drain Current ( $T_J = 150^\circ\text{C}$ ) (Note 1) $T_A = 25^\circ\text{C}$ $T_A = 85^\circ\text{C}$	$I_D$	$\pm 2.9$ $\pm 2.1$	$\pm 2.1$ $\pm 1.5$	A
Pulsed Drain Current	$I_{DM}$	$\pm 10$		A
Continuous Source Current (Diode Conduction) (Note 1)	$I_S$	-1.8	-0.9	A
Maximum Power Dissipation (Note 1) $T_A = 25^\circ\text{C}$ $T_A = 85^\circ\text{C}$	$P_D$	2.1 1.1	1.1 0.6	W
Operating Junction and Storage Temperature Range	$T_J, T_{stg}$	-55 to +150		$^\circ\text{C}$

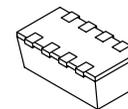
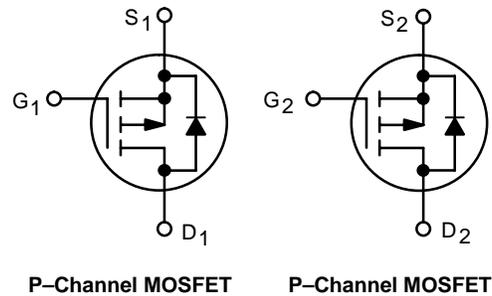
1. Surface Mounted on 1" x 1" FR4 Board.



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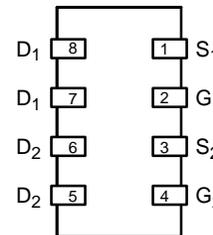
<http://onsemi.com>

**DUAL P-CHANNEL**  
**2.1 AMPS, 20 VOLTS**  
 **$R_{DS(on)} = 155 \text{ m}\Omega$**

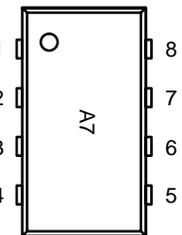


ChipFET  
CASE 1206A  
STYLE 2

#### PIN CONNECTIONS



#### MARKING DIAGRAM



A7 = Specific Device Code

#### ORDERING INFORMATION

Device	Package	Shipping
NTHD5903T1	ChipFET	3000/Tape & Reel

# NTHD5903T1

## THERMAL CHARACTERISTICS

Characteristic	Symbol	Typ	Max	Unit
Maximum Junction-to-Ambient (Note 2) $t \leq 5$ sec Steady State	$R_{thJA}$	50 90	60 110	$^{\circ}\text{C/W}$
Maximum Junction-to-Foot (Drain) Steady State	$R_{thJF}$	30	40	$^{\circ}\text{C/W}$

## ELECTRICAL CHARACTERISTICS ( $T_J = 25^{\circ}\text{C}$ unless otherwise noted)

Characteristic	Symbol	Test Condition	Min	Typ	Max	Unit
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### Static

Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = -250 \mu\text{A}$	-0.6	-	-	V
Gate-Body Leakage	$I_{GSS}$	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 12 \text{ V}$	-	-	$\pm 100$	nA
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS} = -16 \text{ V}, V_{GS} = 0 \text{ V}$	-	-	-1.0	$\mu\text{A}$
		$V_{DS} = -16 \text{ V}, V_{GS} = 0 \text{ V}, T_J = 85^{\circ}\text{C}$	-	-	-5.0	
On-State Drain Current (Note 3)	$I_{D(on)}$	$V_{DS} \leq -5.0 \text{ V}, V_{GS} = -4.5 \text{ V}$	-10	-	-	A
Drain-Source On-State Resistance (Note 3)	$r_{DS(on)}$	$V_{GS} = -4.5 \text{ V}, I_D = -2.1 \text{ A}$	-	0.130	0.155	$\Omega$
		$V_{GS} = -3.6 \text{ V}, I_D = -2.0 \text{ A}$	-	0.150	0.180	
		$V_{GS} = -2.5 \text{ V}, I_D = -1.7 \text{ A}$	-	0.215	0.260	
Forward Transconductance (Note 3)	$g_{fs}$	$V_{DS} = -10 \text{ V}, I_D = -2.1 \text{ A}$	-	5.0	-	S
Diode Forward Voltage (Note 3)	$V_{SD}$	$I_S = -0.9 \text{ A}, V_{GS} = 0 \text{ V}$	-	-0.8	-1.2	V

### Dynamic (Note 4)

Total Gate Charge	$Q_g$	$V_{DS} = -10 \text{ V}, V_{GS} = -4.5 \text{ V}, I_D = -2.1 \text{ A}$	-	3.0	6.0	nC
Gate-Source Charge	$Q_{gs}$		-	0.9	-	
Gate-Drain Charge	$Q_{gd}$		-	0.6	-	
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = -10 \text{ V}, R_L = 10 \Omega, I_D \cong -1.0 \text{ A}, V_{GEN} = -4.5 \text{ V}, R_G = 6 \Omega$	-	13	20	ns
Rise Time	$t_r$		-	35	55	
Turn-Off Delay Time	$t_{d(off)}$		-	25	40	
Fall Time	$t_f$		-	25	40	
Source-Drain Reverse Recovery Time	$t_{rr}$	$I_F = -0.9 \text{ A}, di/dt = 100 \text{ A}/\mu\text{s}$	-	40	80	

2. Surface Mounted on 1" x 1" FR4 Board.
3. Pulse Test: Pulse Width  $\leq 300 \mu\text{s}$ , Duty Cycle  $\leq 2\%$ .
4. Guaranteed by design, not subject to production testing.

TYPICAL ELECTRICAL CHARACTERISTICS

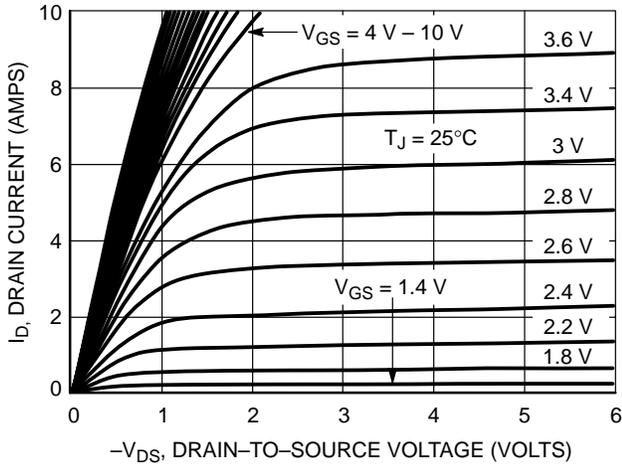


Figure 1. On-Region Characteristics

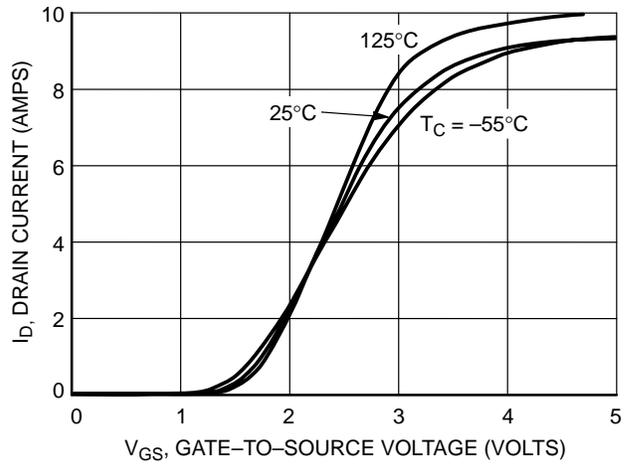


Figure 2. Transfer Characteristics

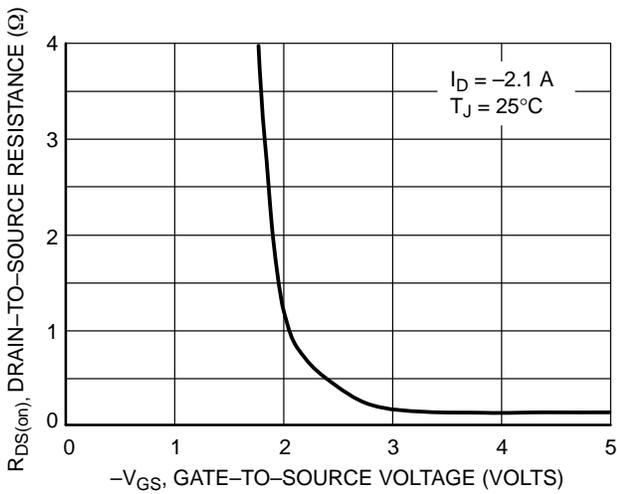


Figure 3. On-Resistance vs. Gate-to-Source Voltage

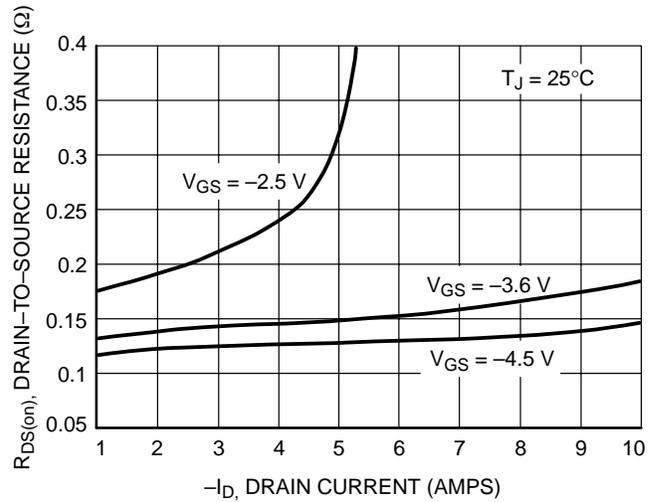


Figure 4. On-Resistance vs. Drain Current and Gate Voltage

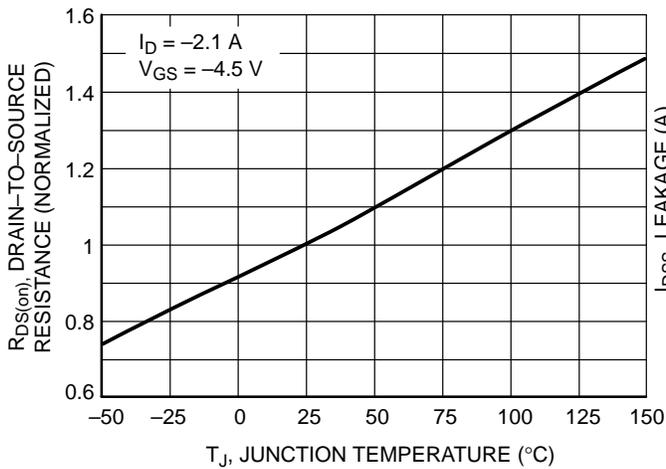


Figure 5. On-Resistance Variation with Temperature

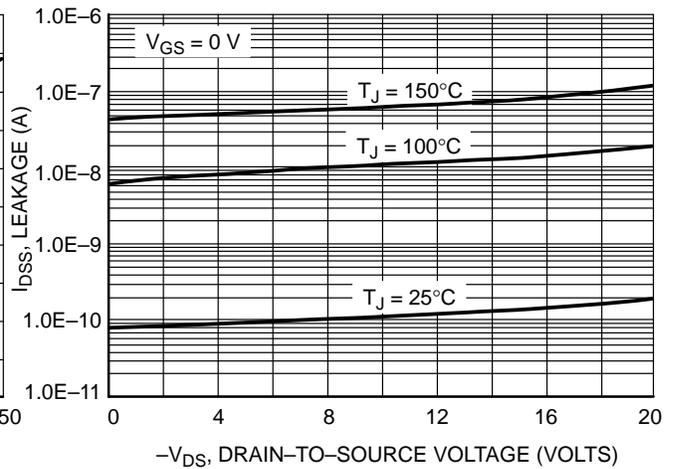


Figure 6. Drain-to-Source Leakage Current vs. Voltage

TYPICAL ELECTRICAL CHARACTERISTICS

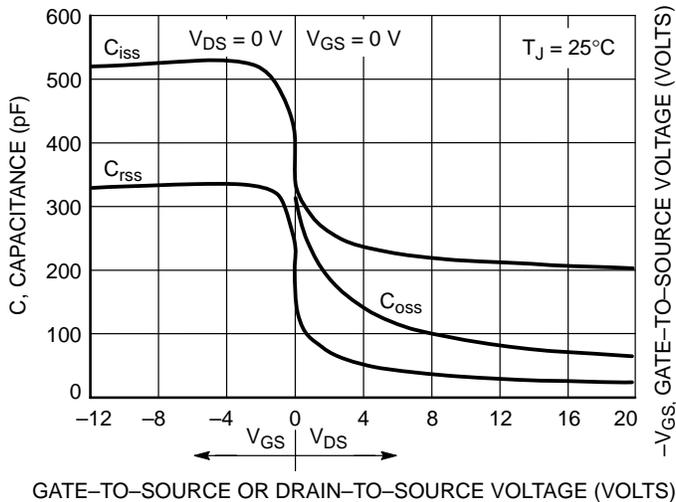


Figure 7. Capacitance Variation

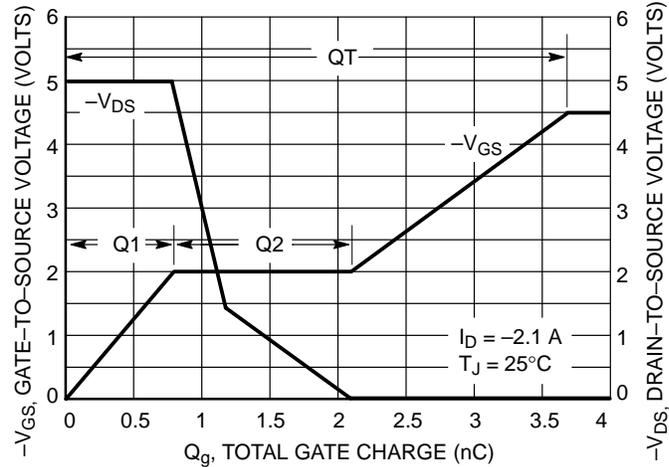


Figure 8. Gate-to-Source and Drain-to-Source Voltage vs. Total Charge

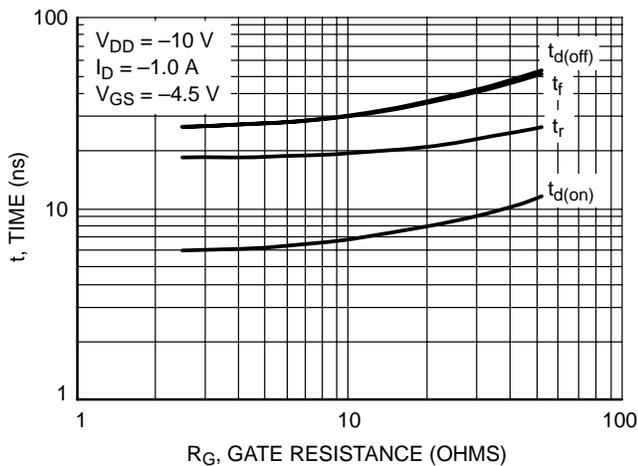


Figure 9. Resistive Switching Time Variation vs. Gate Resistance

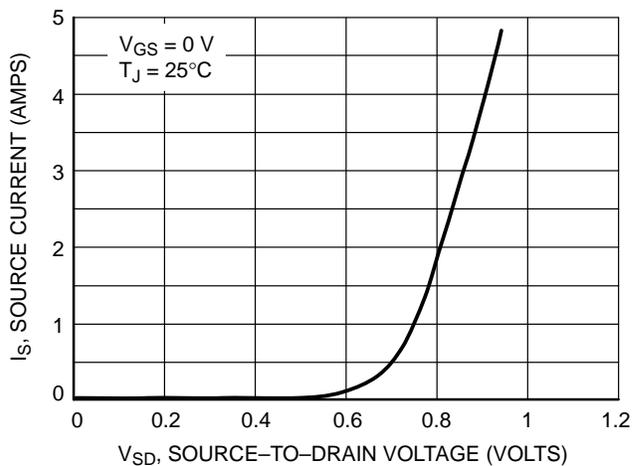


Figure 10. Diode Forward Voltage vs. Current

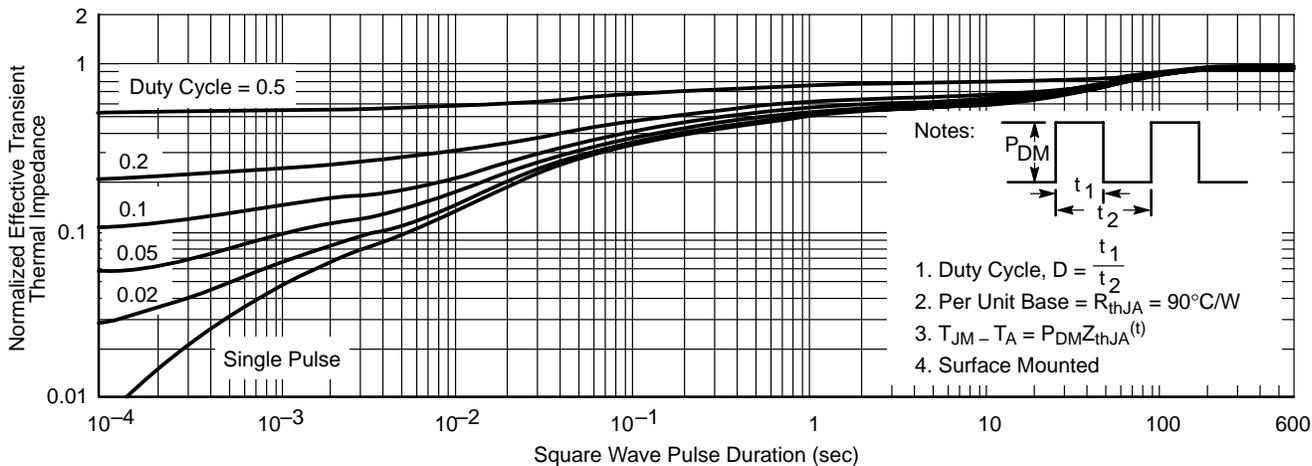


Figure 11. Normalized Thermal Transient Impedance, Junction-to-Ambient

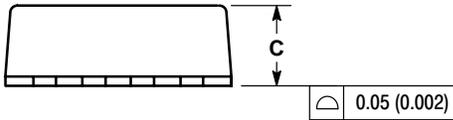
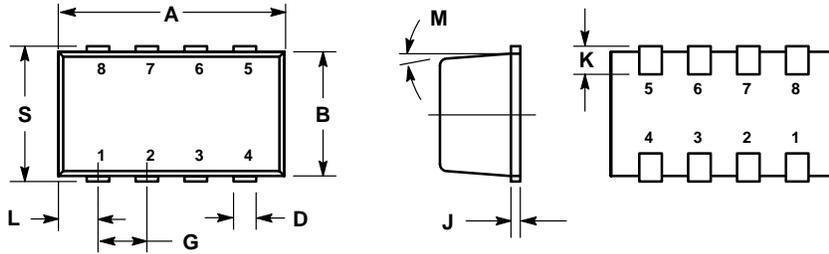
**Notes**

**Notes**

# NTHD5903T1

## PACKAGE DIMENSIONS

ChipFET  
CASE 1206A-03  
ISSUE D



- STYLE 2:  
PIN 1. SOURCE 1  
2. GATE 1  
3. SOURCE 2  
4. GATE 2  
5. DRAIN 2  
6. DRAIN 2  
7. DRAIN 1  
8. DRAIN 1

NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: MILLIMETER.
3. MOLD GATE BURRS SHALL NOT EXCEED 0.13 MM PER SIDE.
4. LEADFRAME TO MOLDED BODY OFFSET IN HORIZONTAL AND VERTICAL SHALL NOT EXCEED 0.08 MM.
5. DIMENSIONS A AND B EXCLUSIVE OF MOLD GATE BURRS.
6. NO MOLD FLASH ALLOWED ON THE TOP AND BOTTOM LEAD SURFACE.
7. 1206A-01 AND 1206A-02 OBSOLETE. NEW STANDARD IS 1206A-03.

DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	2.95	3.10	0.116	0.122
B	1.55	1.70	0.061	0.067
C	1.00	1.10	0.039	0.043
D	0.25	0.35	0.010	0.014
G	0.65 BSC		0.025 BSC	
J	0.10	0.20	0.004	0.008
K	0.28	0.42	0.011	0.017
L	0.55 BSC		0.022 BSC	
M	5° NOM		5° NOM	
S	1.80	2.00	0.072	0.080

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